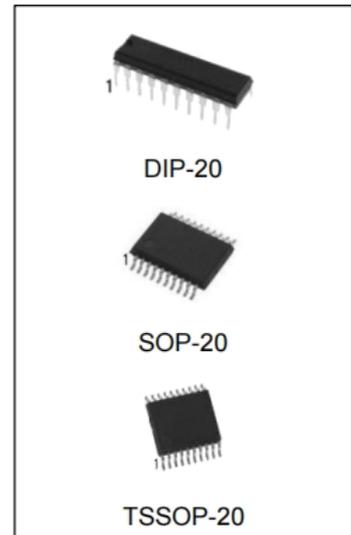


General Description

The 74HCT541 is an 8-bit inverting buffer/line driver with 3-state outputs. The device features two output enables ($\overline{OE1}$ and $\overline{OE2}$). A HIGH on $\overline{OE n}$ causes the outputs to assume a high-impedance OFF-state. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of VCC.

Features

- Input levels: CMOS level
- Inverting outputs
- Specified from -40°C to +105°C
- Packaging information: DIP-20/SOP-20/TSSOP-2



Ordering Information

Product Model	Package Type	Marking	Packing	Packing Qty
74HC541N	DIP-20	74HC541	TUBE	720pcs/box
74HC541M/TR	SOP-20	74HC541	REEL	2000pcs/reel
74HC541MT/TR	TSSOP-20	HC541	REEL	2500pcs/reel

Block Diagram

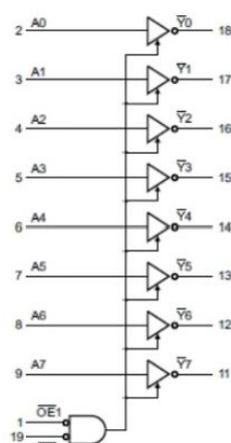


Figure 1. Logic symbol

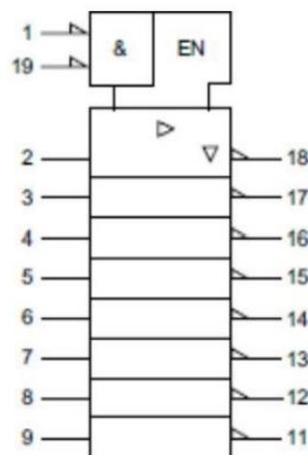


Figure 2. IEC logic symbol

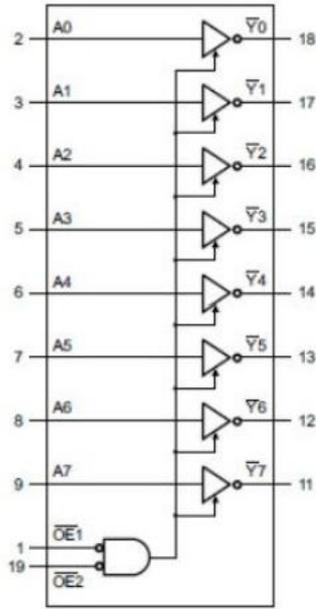


Figure 3. Functional diagram

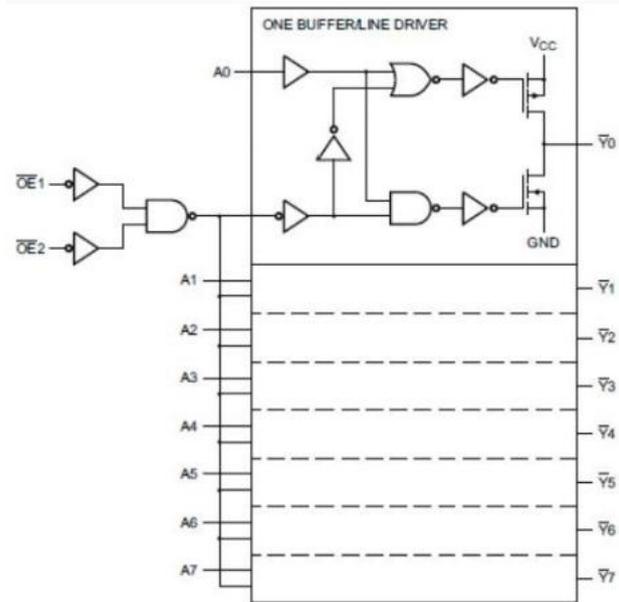
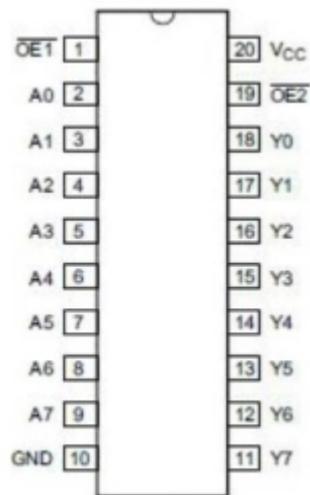


Figure 4. Logic diagram

Pin Configurations



DIP-20/SOP-20/TSSOP-20

Pin Description

Pin No.	Pin Name	Description
1	OE	output enable input (active LOW)
2	Q0	data output
3	D0	data input
4	D1	data input
5	Q1	data output
6	Q2	data output
7	D2	data input
8	D3	data input
9	Q3	data output
10	GND	ground (0V)
11	CP	clock input (LOW-to-HIGH,edge-triggered)
12	Q4	data output
13	D4	data input
14	D5	data input
15	Q5	data output
16	Q6	data output
17	D6	data input
18	D7	data input
19	Q7	data output
20	Vcc	supply voltage

Function Table

Input			Output
OE1	OE2	An	Yn
L	L	L	H
L	L	H	L
X	H	X	Z
H	X	X	Z

Note:

H=HIGH voltage level;L=LOW voltage level;X=don't care;Z=high-impedance OFF-state.

Electrical Parameter

Absolute Maximum Ratings

(Voltages are referenced to GND(ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions	Min	Max	Unit
supply voltage	VCC		-0.5	+7.0	V
input clamping current	I _{IK}	V _i <-0.5V or V _i >V _{CC} +0.5V		±20	mA
output clamping current	I _{OK}	V _o <-0.5V or V _o >V _{CC} +0.5V		±20	mA
output current	I _o	-0.5V<V _o <V _{CC} +0.5V		±35	mA
supply current	I _{CC}			70	mA
ground current	I _{GND}		-70		mA
storage temperature	T _{stg}		-65	+150	°C
total power dissipation	P _{tot}			500	mW
Soldering temperature	TL	10s	DIP	245	°C
			SOP	245	

Note:1. Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured.

2. For DIP20 packages: above 70°C the value of P_{tot} derates linearly with 12mW/K.

3. For SOP20 packages: above 70°C the value of P_{tot} derates linearly with 8mW/K.

4. For TSSOP20 packages: above 60°C the value of P_{tot} derates linearly with 5.5mW/K.

Recommended Operating Conditions

Parameter	Symbol	Conditions	Min	Typ	Max.	Unit
supply voltage	V _{CC}		2.0	5.0	6.0	V
input voltage	V _i		0	—	V _{CC}	V
output voltage	V _o		0		V _{CC}	V
input transition rise and fall rate	ΔtΔV	V _{CC} =2.0V			625	nsN
		V _{CC} =4.5V		1.67	139	nsN
		V _{CC} =6.0V		—	83	nsN
ambient temperature	T _{amb}		-40		+105	°C

Electrical Characteristics

DC Characteristics 1

(Tamb=25°C, voltages are referenced to GND(ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
HIGH-level input voltage	VH	Vcc=2.0V	1.5	1.2		V	
		Vcc=4.5V	3.15	2.4		V	
		Vcc=6.0V	4.2	3.2		V	
LOW-level input voltage	VL	Vcc=2.0V		0.8	0.5	V	
		Vcc=4.5V		2.1	1.35	V	
		Vcc=6.0V		2.8	1.8	V	
HIGH-level output voltage	Voh	Vi=Vh or VL	Io=-20uA;Vcc=2.0V	1.9	2.0		V
			Io=-20uA;Vcc=4.5V	4.4	4.5		V
			Io=-20uA;Vcc=6.0V	5.9	6.0		V
			Io=-6.0mA;Vcc=4.5V	3.98	4.32		V
			Io=-7.8mA;Vcc=6.0V	5.48	5.81		V
LOWlevel output voltage	Vol	Vi=VH or VL	Io=20uA;Vcc=2.0V		0	0.1	V
			Io=20uA;Vcc=4.5V		0	0.1	V
			Io=20uA;Vcc=6.0V		0	0.1	V
			Io=6.0mA;Vcc=4.5V		0.15	0.26	V
			Io=7.8mA;Vcc=6.0V		0.16	0.26	V
input leakage current	I	Vi=Vcc or GND;Vcc=6.0V			±0.1	uA	
OFF-state output current	Ioz	Vi=Vh or VL;Vcc=6.0V; Vo=Vcc or GND			±0.5	uA	
supply current	Icc	Vi=Vcc or GND;Io=0A;Vcc=6.0V			8.0	uA	
input capacitance	Ci			3.5		pF	

DC Characteristics 2

(Tamb=-40°C to +85°C, voltages are referenced to GND(ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
HIGH-level input voltage	ViH	Vcc=2.0V	1.5			V	
		Vcc=4.5V	3.15			V	
		Vcc=6.0V	4.2			V	
LOW-level input voltage	VL	Vcc=2.0V			0.5	V	
		Vcc=4.5V			1.35	V	
		Vcc=6.0V			1.8	V	
HIGH-level output voltage	VoH	Vi=Vh or VL	Io=-20uA;Vcc=2.0V	1.9			V
			Io=-20uA;Vcc=4.5V	4.4			V
			Io=-20uA;Vcc=6.0V	5.9			V
			Io=-6.0mA;Vcc=4.5V	3.84			V
			Io=-7.8mA;Vcc=6.0V	5.34			V
LOW-level output voltage	Vol	Vi=Vh or VL	Io=20uA;Vcc=2.0V			0.1	V
			Io=20uA;Vcc=4.5V			0.1	V
			Io=20uA;Vcc=6.0V			0.1	V
			Io=6.0mA;Vcc=4.5V			0.33	V
			Io=7.8mA;Vcc=6.0V			0.33	V
input leakage current	I	V=Vcc or GND;Vcc=6.0V	—		±1.0	uA	
OFF-state output current	Ioz	Vi=Vih or VL;Vcc=6.0V Vo=Vcc or GND			±5.0	uA	
supply current	Icc	V=Vcc or GND;Io=0A;Vcc=6.0V			80	uA	

DC Characteristics 3

(Tamb=40°C to +105°C, voltages are referenced to GND(ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ.	Max	Unit	
HIGH-level input voltage	V _H	V _{CC} =2.0V	1.5			V	
		V _{CC} =4.5V	3.15			V	
		V _{CC} =6.0V	4.2			V	
LOW-level input voltage	V _L	V _{CC} =2.0V			0.5	V	
		V _{CC} =4.5V			1.35	V	
		V _{CC} =6.0V			1.8	V	
HIGH-level output voltage	V _{OH}	V _i =V _{ih} or V _L	I _o =-20μA;V _{CC} =2.0V	1.9			V
			I _o =-20μA;V _{CC} =4.5V	4.4			V
			I _o =-20μA;V _{CC} =6.0V	5.9			V
			I _o =-6.0mA;V _{CC} =4.5V	3.7			V
			I _o =-7.8mA;V _{CC} =6.0V	5.2			V
LOW-level output voltage	V _{OL}	V _i =V _{ih} or V _L	I _o =20μA;V _{CC} =2.0V			0.1	V
			I _o =20μA;V _{CC} =4.5V			0.1	V
			I _o =20μA;V _{CC} =6.0V			0.1	V
			I _o =6.0mA;V _{CC} =4.5V			0.4	V
			I _o =7.8mA;V _{CC} =6.0V			0.4	V
input leakage current	I _I	V=V _{CC} or GND;V _{CC} =6.0V			±1.0	μA	
OFF-state output current	I _{OZ}	V _i =V _{ih} or V _L ;V _{CC} =6.0V; V _o =V _{CC} or GND			±10	μA	
supply current	I _{CC}	V=V _{CC} or GND;I _o =0A;V _{CC} =6.0V	—		160	μA	

AC Characteristics 1

(Tamb=25°C, GND=0V, CL=50pF, unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ.	Max	Unit	
An to Yn propagation delay	tpd	see Figure 6	Vcc=2.0V		33	115	ns
			Vcc=4.5V		12	23	ns
			Vcc=5.0V;CL=15pF		10		ns
			Vcc=6.0V		10	20	ns
OEn to Yn enable time	ten	see Figure 7	Vcc=2.0V		55	160	ns
			Vcc=4.5V		20	32	ns
			Vcc=6.0V		16	27	ns
OEn to Yn disable time	tis	see Figure 7	Vcc=2.0V		61	160	ns
			Vcc=4.5V		22	32	ns
			Vcc=6.0V		18	27	ns
transition time	tt	see Figure 6	Vcc=2.0V		14	60	ns
			Vcc=4.5V		5	12	ns
			Vcc=6.0V		4	10	ns
power dissipation capacitance	CPD	per buffer;Vi=GND to Vcc		37		pF	

Note:

1. tpa is the same as tpLhand tpHL.
2. ten is the same as tpzt and tpzH.
3. tais is the same as tpuz and tpHz.
4. t is the same as trhand truh.
5. Cro is used to determine the dynamic power dissipation (Po in uW)

$P_o = C_{pp} \times V_{cc}^2 \times f_i \times N + Z(C \times V_{cc}^2 \times f_o)$ where:

fi=input frequency in MHz;

fo=output frequency in MHz;

CL=output load capacitance in pF;

Vcc=supply voltage in V;

N=number of inputs switching;

Z(Ct × Vcc² × fo)=sum of outputs.

AC Characteristics 2

(Tamb=-40°C to+85°C, GND=0V, CL=50pF, unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
An to Yn propagation delay	tpd	see Figure 6	Vcc=2.0V		145	ns
			Vcc=4.5V		29	ns
			Vcc=6.0V		25	NS
OEn to Yn enable time	ten	see Figure 7	Vcc=2.0V		200	NS
			Vcc=4.5V		40	ns
			Vcc=6.0V		34	ns
OEn to Yn disable time	tis	see Figure 7	Vcc=2.0V		200	NS
			Vcc=4.5V		40	NS
			Vcc=6.0V		34	ns
transition time	t	see Figure 6	Vcc=2.0V		75	ns
			Vcc=4.5V		15	ns
			Vcc=6.0V		13	ns

Note:

1. tra is the same as tpuhand tpHl
2. ten is the same as tpzt and tpzH.
3. tis is the same as tpuzandtpHz.
4. t is the same as trhland truh.

AC Characteristics 3

(Tamb=-40°C to +105°C, GND=0V, CL=50pF, unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
An to Yn propagation delay	tpd	see Figure 6	Vcc=2.0V		175	ns
			Vcc=4.5V		35	ns
			Vcc=6.0V		30	ns
OEn to Yn enable time	ten	see Figure 7	Vcc=2.0V		240	ns
			Vcc=4.5V		48	ns
			Vcc=6.0V		41	ns
OEn to Yn disable time	tis	see Figure 7	Vcc=2.0V		240	ns
			Vcc=4.5V		48	ns
			Vcc=6.0V		41	ns
transition time	t	see Figure 6	Voc=2.0V		90	ns
			Vcc=4.5V		18	ns
			Vcc=6.0V		15	ns

Note:

1. tu is the same as truhand tpHL.
2. ten is the same as tez and tpzh.
3. tas is the same as tpuzandtpHz.
4. t is the same as trhland truh.

Testing Circuit

AC Testing Circuit

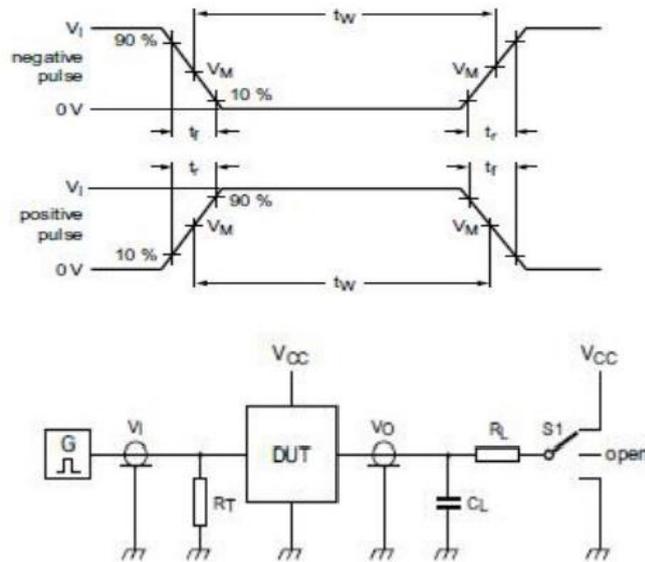


Figure 5. Test circuit for measuring switching times

Definitions for test circuit:

R_L =Load resistance.

C_L =Load capacitance including jig and probe capacitance.

R_T =Termination resistance should be equal to the output impedance Z_o of the pulse generator. S_1 =Test selection switch.

AC Testing Waveforms

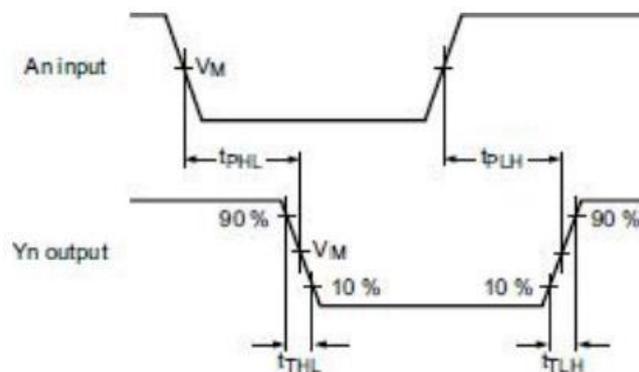
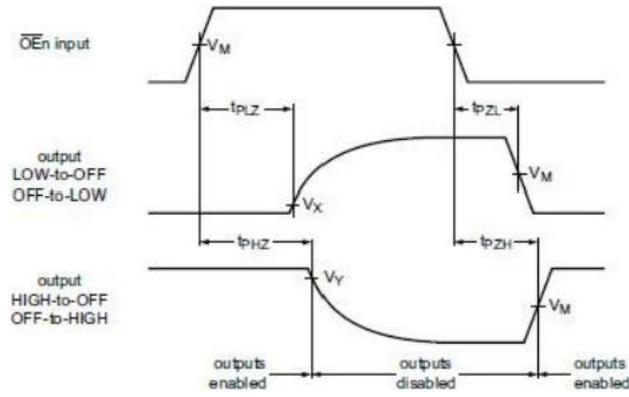


Figure 6. Input to output propagation delays


Figure 7.3-3-state enable and disable times
Measurement Points

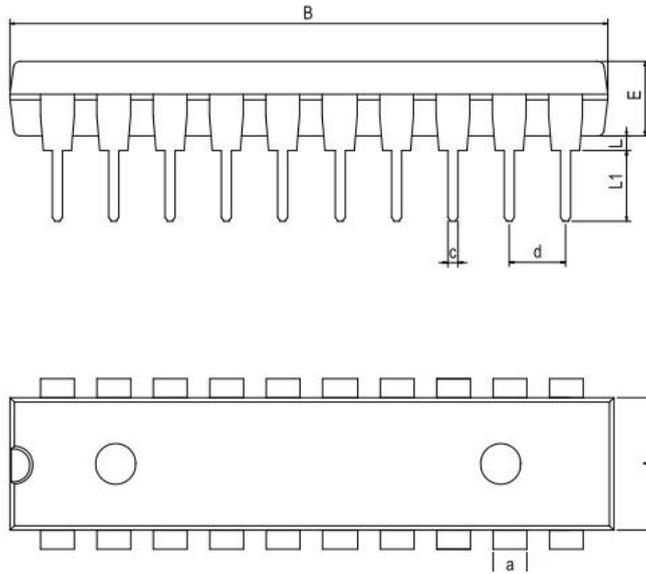
Type	Input	Output		
	VM	VM	Vx	Vy
74HC541	0.5×Vcc	0.5×Vcc	0.1×Vcc	0.9×Vc

Test Data

Type	Input		Load		S1 position		
	v _i	tr, tr	CL	RL	tpHL tpLH	tezH tpHz	tpzI tpLz
74HC541	Vcc	6ns	15pF, 50pF	1kΩ	open	GND	Vcc

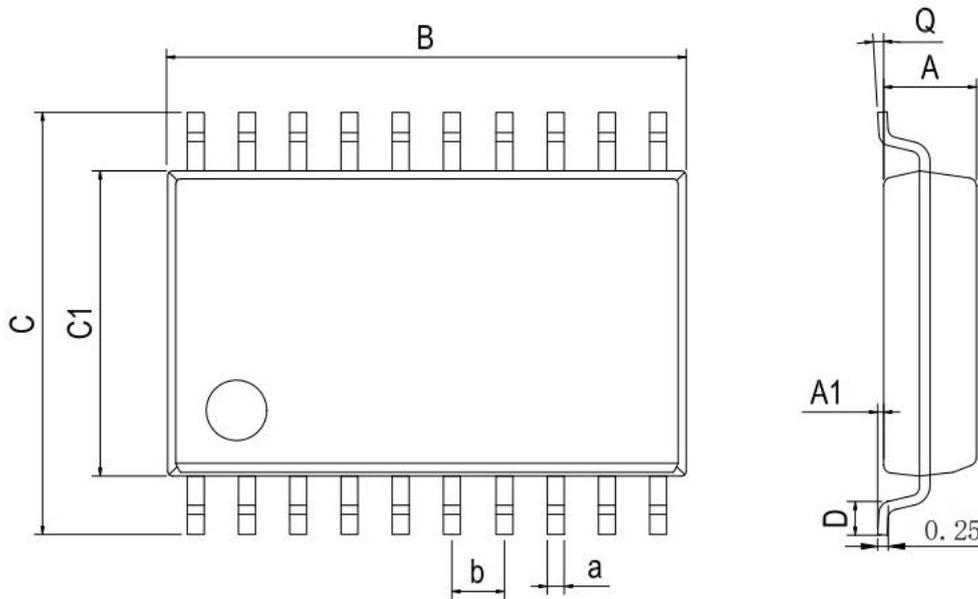
Physical Dimensions

DIP-20



Dimensions In Millimeters(DIP-20)										
Symbol:	A	B	D	D1	E	L	L1	a	C	d
Min:	6.10	24.95	8.10	7.42	3.10	0.50	3.00	1.50	0.40	2.54 BSC
Max:	6.68	26.55	10.9	7.82	3.55	0.70	3.60	1.55	0.50	

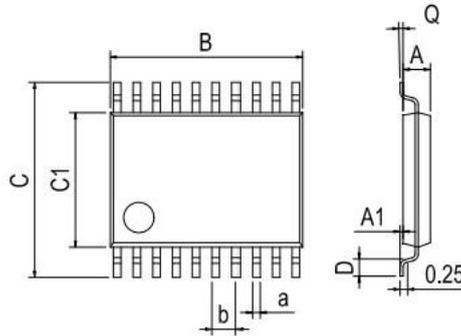
SOP-20



Dimensions In Millimeters(SOP-20)									
Symbol:	A	A1	B	C	C1	D	Q	a	b
Min:	2.10	0.05	12.50	10.21	7.40	0.45	0°	0.35	1.27 BSC
Max:	2.50	0.25	13.00	10.61	7.60	1.25	8°	0.45	

Physical Dimensions

TSSOP-20



Dimensions In Millimeters(TSSOP-20)									
Symbol:	A	A1	B	C	C1	D	Q	a	b
Min:	0.85	0.05	6.40	6.20	4.30	0.40	0°	0.20	0.65 BSC
Max:	1.05	0.20	6.60	6.60	4.50	0.80	8°	0.25	